查询2N7372供应商

PPC, Inc.
Microsemi
Progress Powered by Technology

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2N7372 - PNP
2N7373 - NPN

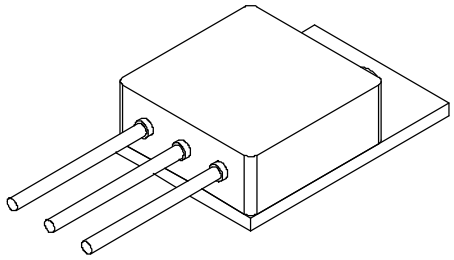
Complimentary Power Transistors in Hermetic Isolated TO-254AA Packages JAN/TX/TXV/JANS

APPLICATIONS:

- Power Supply
- Inverters and Converters
- General Purpose Amplifiers

FEATURES:

- Planar Process for Reliability
- Fast Switching
- High-Frequency Power Transistors
- For Complementary Use with Each Other
- 15 mj Reverse Energy Rating with I_C = 10MA and 4 V Reverse Bias
- Similar to 2N5004 and 2N5005 but JEDEC TO-254AA Package
- Leads can be Formed
- All Terminals Isolated from the Case



TO-254AA

DESCRIPTION:

These power transistors are produced by PPC's MULTIPLE DIFFUSED PLANAR process. This technology produces high voltage devices with excellent switching speeds, frequency response, gain linearity, saturation voltages, high current gain, and safe operating areas. These devices have excellent unclamped and clamped reverse energy ratings with the base to emitter reversed biased.

Ultrasonically bonded wire leads and gold eutectic die bonding are utilized to permit operating temperature to 200°C. The hermetically sealed package insures maximum reliability and long life. The isolated low profile package allows for easy PC board fit.

ABSOLUTE MAXIMUM RATINGS:

SYMBOL	CHARACTERISTIC	2N7372	2N7373	UNITS
V_{CBO}	Collector-Base Voltage	- 100	100	V
V_{CEO}	Collector-Emitter Voltage	- 80	80	V
V_{EBO}	Emitter-Base Voltage	- 5.5	5.5	V
I_C	Continuous Collector Current	5	5	A
I_C	Peak Collector Current	10	10	A
I_B	Continuous Base Current	2	2	A
T_{STG}	Storage Temperature	-65 to 200		°C
T_J	Operating Junction Temperature	-65 to 200		°C
	Lead Temperature 1/16" from cast for 10 sec.	300		°C
	Unclamped Inductive Load Energy	15		mj
P_T	Continuous Device			
	Dissipation T_C = 25°C	58	58	W
	T_C = 100°C	33	33	W
θJC	Thermal Resistance Junction to Case	3	3	°C/W

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ELECTRICAL CHARACTERISTICS:
(25°Case Temperature Unless Otherwise Noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VALUE		Units
			Min.	Max.	
V_{CEO}	Collector-Emitter Breakdown Voltage	I_C = 100 mA, I_B = 0	80	----	V
I_{CEO}	Collector Cutoff Current, Base Open	I_B = 0, V_{CE} = 40 V	----	50	µA
I_{CES}	Collector Cutoff Current, Emitter-Base Short	V_{CE} = 100 V	----	1	mA
		V_{CE} = 60 V	----	1	µA
I_{CEX}	Collector Cutoff Current	V_{BE} = 60 V, VBE = 2 V, T_C = 150°C	----	500	µA
I_{EBO}	Emitter Cutoff Current	V_{EB} = 5.5 V, I_C =0	----	1	mA
		V_{EB} = 4.0 V, I_C =0	----	1	µA
HFE	Static Forward Current Transfer Ratio	I_C = 5.0 A, V_{CE} = 5.0 V	40	----	----
		I_C = 2.5 A, V_{CE} = 5.0 V	70	200	----
		I_C = 2.5 A, V_{CE} = 5.0 V, T_C = -55°C	25	----	----
		I_C = 50 mA, V_{CE} = 5.0 V	50	----	----
V_{BE}	Base-Emitter Volatage	I_C = 2.5 A, V_{CE} = 5.0 V	----	1.45	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C = 2.5 A, I_B = 0.25 A	----	1.45	V
		I_C = 5.0 A, I_B = 0.5 A	----	2.2	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C = 5.0 A, I_B = 0.5 A	----	1.5	V
		I_C = 2.5 A, I_B = 0.25 A	----	0.75	----
HFE	Small Signal Common-Emitter Forward Current Transfer Ratio	V_{CE} = 5.0 V, I_C = 100 mA, F = 1.0 KHz	50	----	----
Ihfel	Small Signal Common Emitter Forward Current Transfer Ratio	V_{CE} = 5.0 V, I_C = 0.5A, F = 10 MHz	7.0	----	----
C_{OBO}	Open-Circuit Output Capacitance	V_{CB} = 10 V, I_E = 0A, F = 0.1 MHz	----	250	pF
t_{on}	Turn-on Time	I_C = 5.0 A, I_{B1} = I_{B2} = 0.5 A	----	0.5	µs
t_{off}	Turn-off Time	V_{BE} (OFF) = 3.7V	----	1.5	µs

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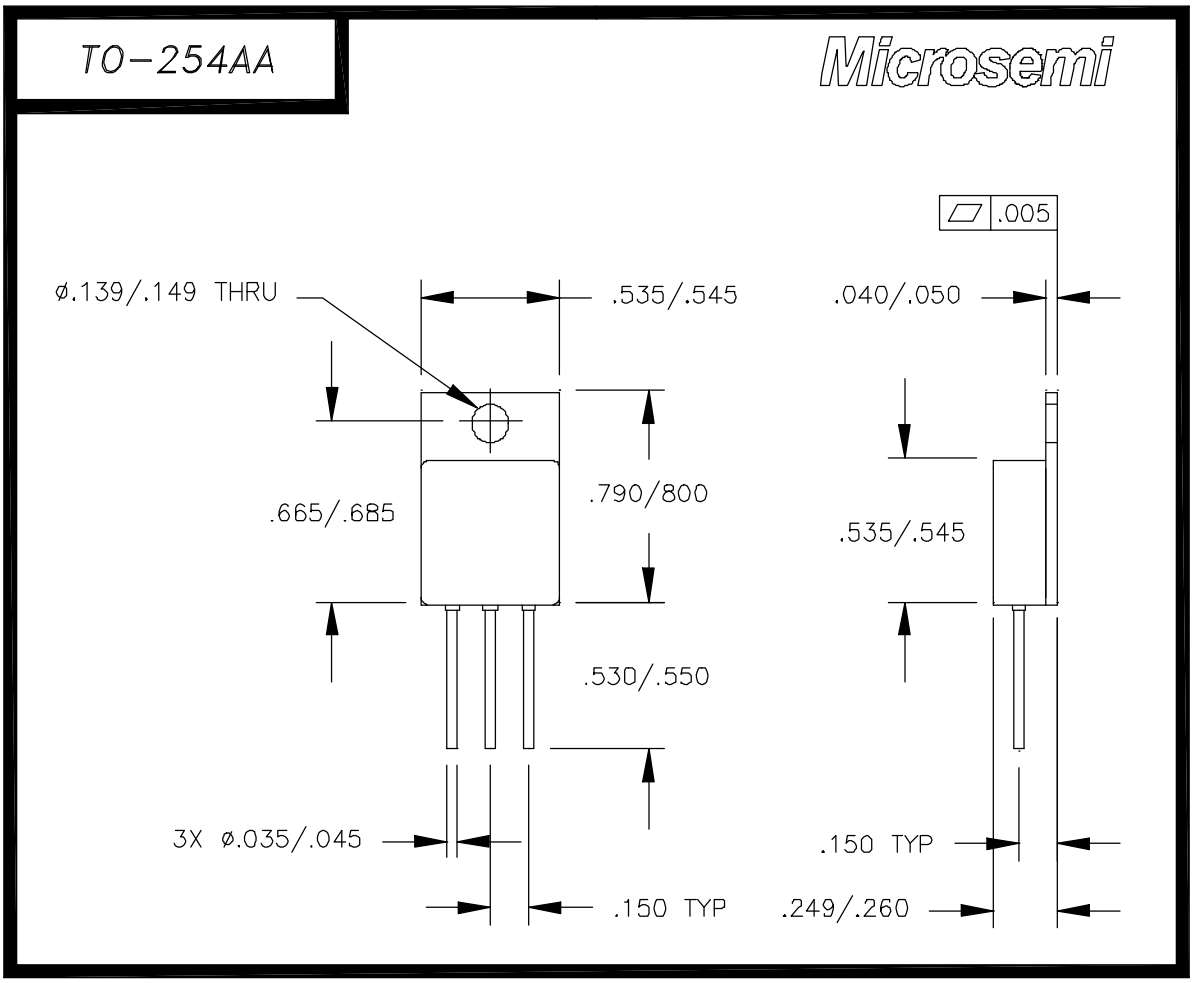
PACKAGE MECHANICAL DATA:



JEDEC Hermetic Metal TO-254AA 3-Pin